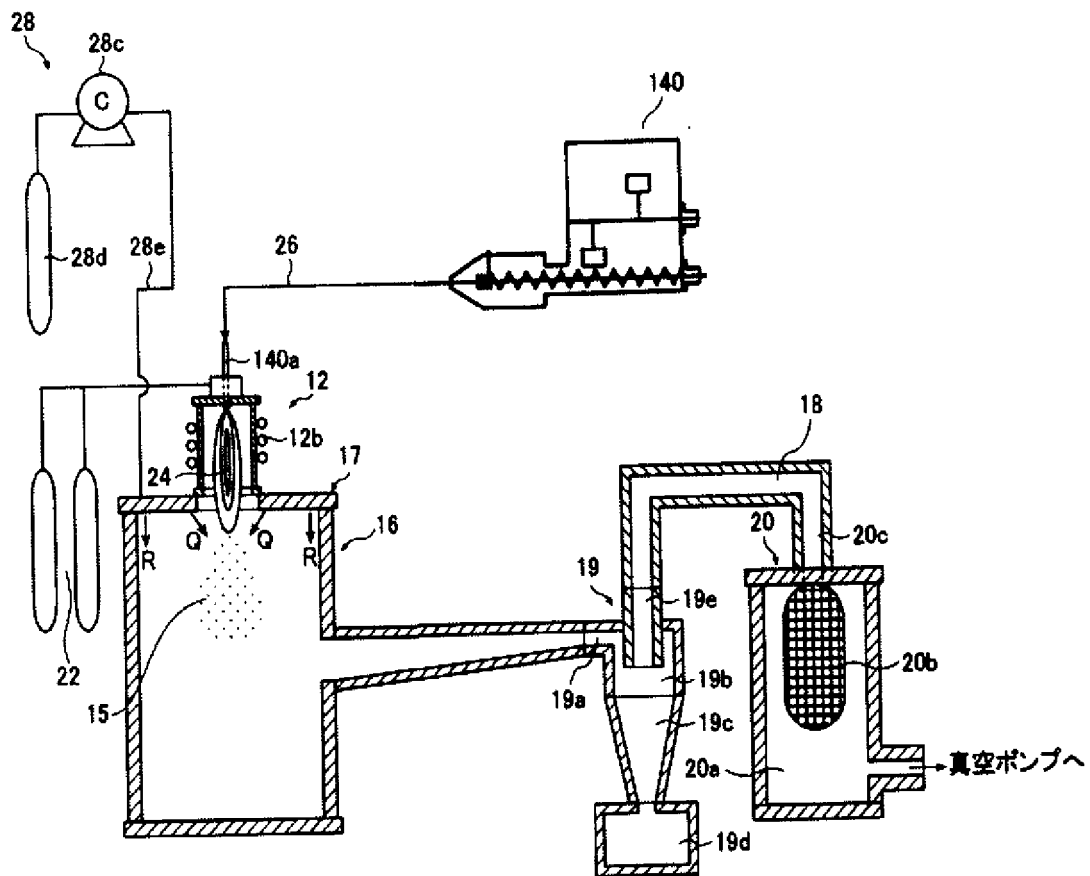
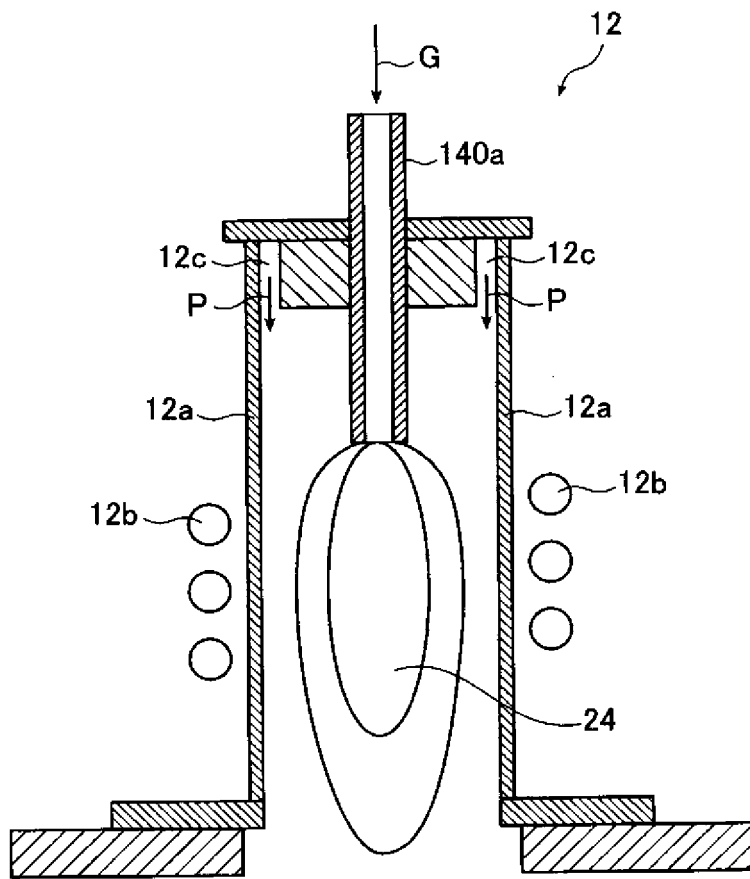


[図1]

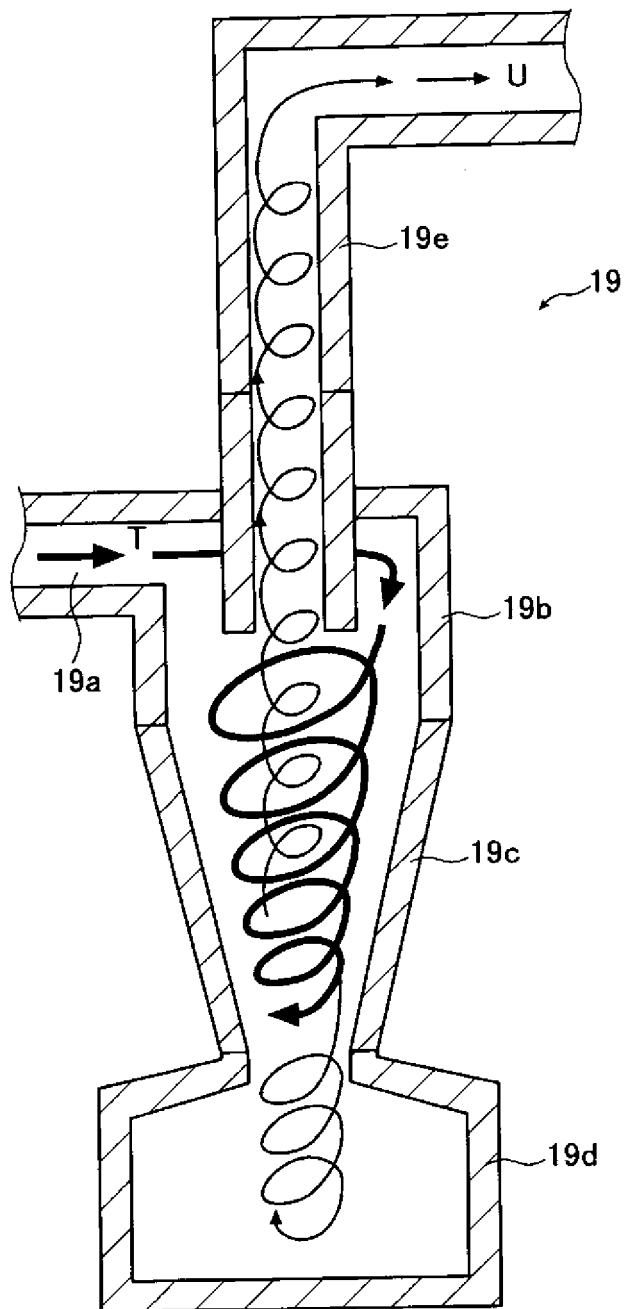


[図2]



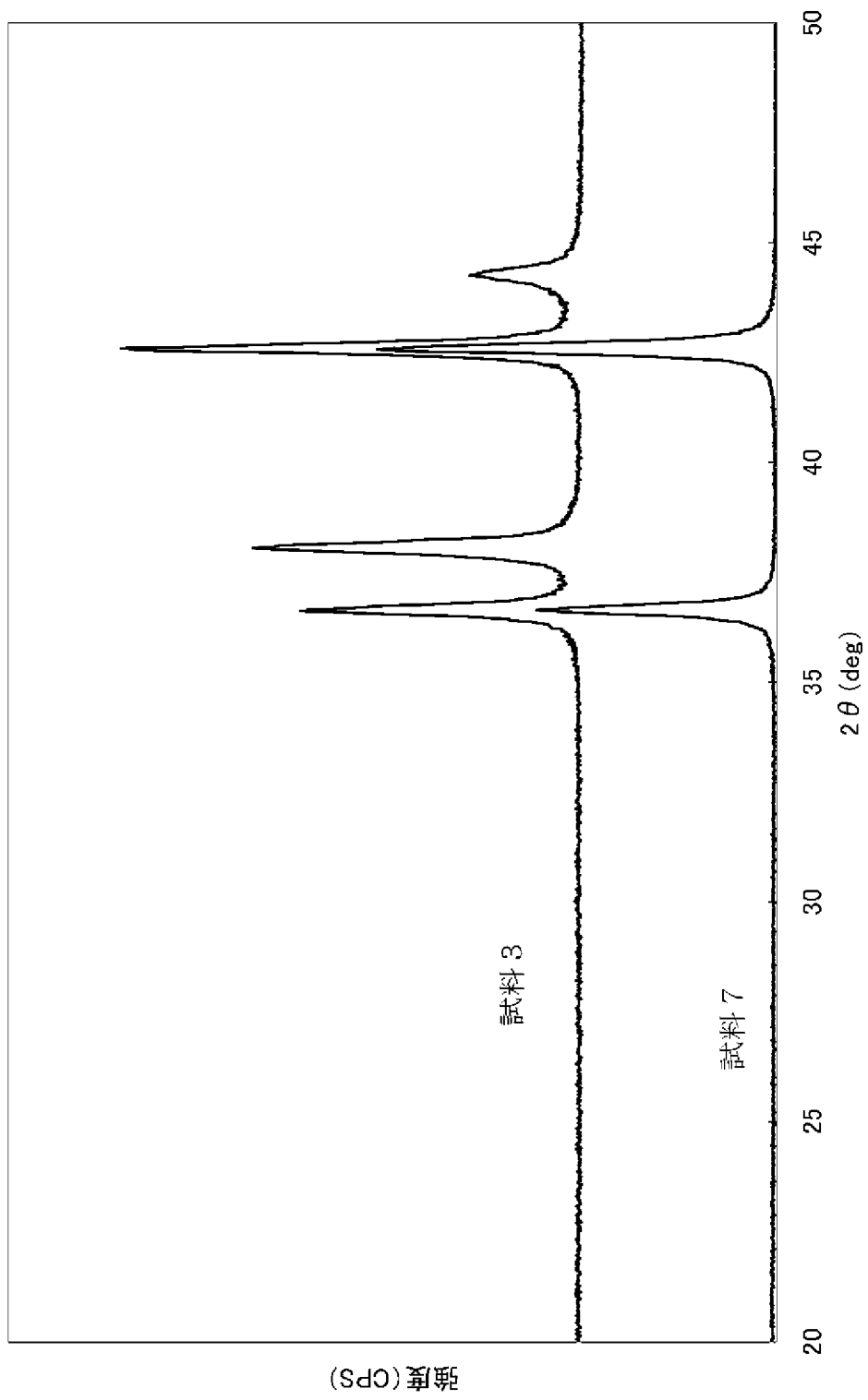
The diagram shows a symmetrical cross-section of a semiconductor device. Two main vertical sections are separated by a central gap. Each section consists of a substrate 17 divided into four horizontal layers: 17a (top), 17b (middle), 17c (lower middle), and 17d (bottom). In the center of each section is a component labeled 24, which has a bell-shaped profile extending through layers 17a and 17b. To the left of each section, an arrow labeled 'S' points towards the device, connected to a line labeled 28e. To the right, an arrow labeled 'R' points away from the device, connected to a line labeled 28b. Within the substrate layers, there are additional labels: 28a points to a region between the central component and the right edge, and 28e also points to a region near the bottom of the substrate.

[図4]





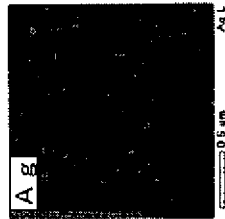
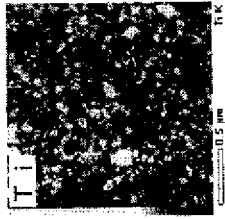
[図6]



[図7]



参考例 2



実施例 3

